

# **Enhancement Of Indium Tin Oxide Nano-Scale Films For Terahertz Device Applications Treated By Rapid Thermal Annealing**

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#### Motivation

## Introduction

- terahertz Evaluated (THz) the optical and electrical properties of ITO nano-thick film treated by RTA Displayed the THz transmittance of different thickness ITO film. The ITO film can be functioned as a THz reflective conductive electrodes by RTA at 600°C Enhanced THz power transmittance from 6 to 49 % at 0.2 THz by RTA at 800°C.
- **THz-TCEs:** poly(3,4-ethylenedioxythiophene) graphene, polystyrene sulfonate and (PEDOT: PSS). **THz-TCEs:** Drawbacks in conductivity and lithography process ITO or Metal finger type pattern: highly sensitive to polarization
- **Requirement:** polarization insensitive, highly conductive and THz transparent electrode for tunable THz devices, Ex. LC-SLM.
- Perhaps, RTA is one of simple way to produce highly efficient either transparent or reflectance electrode.

### **Result and discussions**



#### Frequency (THz) (a) 0.2 0.4 0.8 1.0 0.6 0.2 10.0kV X20.000 WD 10.6mm Frequency (THz) Conclusions References We showed that ITO nano films RTA-annealed at 600°C and 800°C are suitable as perfect absorbers and half-mirrors or electrodes, respectively. Analyzed electrical properties of as-deposited and RTA treated by using Drude model.

The annealing condition further need to be optimizing for enhancing THz transmittance in the frequency range of 0.2-1.2 THz.

[1] A. K. Sahoo et al., "Liquid Crystal Based Terahertz Spatial Light Modulator for Imaging Application," 2018 43rd International Conference on Infrared, Millimeter, and Terahertz Waves (IRMMW-THz), Japan, 2018, pp. 1-2. [2] Z. Shi, L. Song and T. Zhang, "Terahertz reflection and visible light transmission of ITO films affected by annealing temperature and applied in metamaterial absorber" Vaccum vol. 149, pp. 12-18, 2018. [3] C.-W. Chen et al., "Frequency-Dependent Complex Conductivities and Dielectric Responses of Indium Tin Oxide from the Visible to the Far- Infared," IEEE J. Quantum Electron., vol. 46, pp. 1746-1754, 2010.. [4] J.-W. Shi *et al.*, "Millimeter-wave photonic wireless links for very-high data rate communication," NPG Asia Mater., vol. 3, pp. 41–48, 2011.

0.4

0.6

Frequency (THz)

0.8 1.0